

<b>Notice of References Cited</b>	Application/Control No. 10/647,534	Applicant(s)/Patent Under Reexamination DIP ET AL.	
	Examiner Julio J. Maldonado	Art Unit 2823	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,613,677 B1	09-2003	Herbots et al.	438/694
*	C	US-6,589,877 B1	07-2003	Thakur, Randhir P.	438/703
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	M	US-			

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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